# **BLF988**; **BLF988S**

# Power LDMOS transistor Rev. 3 — 1 September 2015

**AMPLEON** 

Product data sheet

#### **Product profile** 1.

### 1.1 General description

A 600 W LDMOS RF power transistor for transmitter applications and industrial applications. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

Table 1. **Application information** 

Test signal	f (MHz)	P <sub>L(AV)</sub> (W)	P <sub>L(M)</sub> (W)	G <sub>p</sub> (dB)	η <sub>D</sub> (%)	IMD3 (dBc)
RF performance in a co	ommon source 860 MHz na	arrowband	l test circ	uit		
2-tone, class-AB	f <sub>1</sub> = 860; f <sub>2</sub> = 860.1	250	-	20.8	46	-32
pulsed, class-AB	860	-	600	19.8	58	-

### 1.2 Features and benefits

- Excellent ruggedness (VSWR ≥ 40 : 1 through all phases)
- Optimum thermal behavior and reliability, R<sub>th(i-c)</sub> = 0.15 K/W
- High power gain
- High efficiency
- Designed for broadband operation (400 MHz to 1000 MHz)
- Internal input matching for high gain and optimum broadband operation
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

# 1.3 Applications

- Communication transmitter applications
- Industrial applications

# 2. Pinning information

Table 2. Pinning

Tubic 2.	i iiiiiiig			
Pin	Description		Simplified outline	Graphic symbol
BLF988 (	SOT539A)			
1	drain1			
2	drain2		1 2	1 . <b></b>
3	gate1		5	3
4	gate2		3 4	5
5	source	[1]		4
				'├─
				2 sym117
BI F988S	(SOT539B)			
	<u> </u>			
1	drain1		1 2	1
2	drain2			نے.
3	gate1		5	ړ ا⊸
4	gate2		3 4	3 - 5
5	source	[1]		4

# 3. Ordering information

Table 3. Ordering information

Type number	Packa	ackage					
	Name	Description	Version				
BLF988	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A				
BLF988S	-	earless flanged balanced ceramic package; 4 leads	SOT539B				

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage			-	110	V
$V_{GS}$	gate-source voltage			-0.5	+11	V
$T_{stg}$	storage temperature			-65	+150	°C
Tj	junction temperature		[1]	-	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability. For details refer to the on-line MTF calculator.

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<sup>[1]</sup> Connected to flange.

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-c)}}$	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_{L(AV)}$ = 250 W	0.15	K/W

<sup>[1]</sup>  $R_{th(j-c)}$  is measured under RF conditions.

## 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.4 \text{ mA}$	[1]	110	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 240 mA	[1]	1.4	1.9	2.4	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$		-	-	2.8	μА
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$		-	36	-	Α
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}$		-	-	280	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 8.5 A$	[1]	-	143	-	mΩ

<sup>[1]</sup> I<sub>D</sub> is the drain current.

Table 7. AC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$ [1]	-	220	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	74	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	1.2	-	pF

<sup>[1]</sup> Capacitance values without internal matching.

### Table 8. RF characteristics

RF characteristics in Ampleon production narrowband test circuit;  $T_{\text{case}} = 25 \, ^{\circ}\text{C}$  unless otherwise specified.

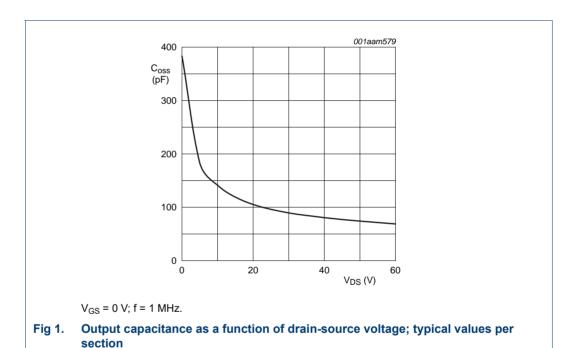
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
2-Tone,	class-AB						
$V_{DS}$	drain-source voltage			-	50	-	V
I <sub>Dq</sub>	quiescent drain current		[1]	-	1.3	-	Α
P <sub>L(AV)</sub>	average output power	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz		250	-	-	W
Gp	power gain	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz		19.8	20.8	-	dB
$\eta_{D}$	drain efficiency	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz		42	46	-	%
IMD3	third-order intermodulation distortion	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz		-	-32	-28	dBc

Table 8. RF characteristics ... continued

RF characteristics in Ampleon production narrowband test circuit;  $T_{case} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Pulsed,	class-AB						
$V_{DS}$	drain-source voltage			-	50	-	V
$I_{Dq}$	quiescent drain current		<u>[1]</u>	-	1.3	-	Α
$P_{L(M)}$	peak output power	f = 860 MHz		-	600	-	W
Gp	power gain	f = 860 MHz		17.2	19.8	-	dB
$\eta_{D}$	drain efficiency	f = 860 MHz		54	58	-	%
t <sub>p</sub>	pulse duration			-	100	-	μS
δ	duty cycle			-	20	-	%

[1] I<sub>Dq</sub> for total device



## 7. Test information

### 7.1 Ruggedness in class-AB operation

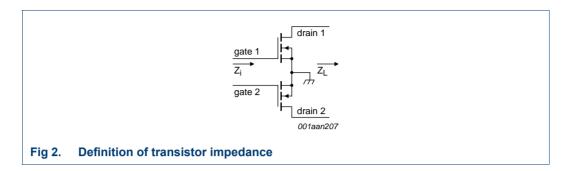
The BLF988 and BLF988S are capable of withstanding a load mismatch corresponding to VSWR  $\geq$  40 : 1 through all phases under the following conditions:  $V_{DS}$  = 50 V;  $I_{Dq}$  = 1.3 A;  $P_L$  = 600 W (pulsed); f = 860 MHz.

# 7.2 Impedance information

Table 9. Typical push-pull impedance

Simulated  $Z_i$  and  $Z_L$  device impedance; impedance info at  $V_{DS} = 50 \text{ V}$  and  $P_{L(AV)} = 600 \text{ W}$  (pulsed CW). See Figure 2 for definition of transistor impedance.

f	<b>Z</b> i	$\mathbf{Z}_{L}$
MHz	Ω	Ω
300	0.607 + j0	5.495 + j1.936
325	0.622 - j1.441	5.324 + j2.008
350	0.639 – j1.121	5.151 + j2.065
375	0.658 - j0.826	4.977 + j2.107
400	0.679 - j0.551	4.805 + j2.136
425	0.703 - j0.291	4.634 + j2.153
450	0.73 - j0.044	4.466 + j2.157
475	0.76 + j0.194	4.301 + j2.151
500	0.793 + j0.424	4.14 + j2.134
525	0.83 + j0.648	3.984 + j2.109
550	0.872 + j0.869	3.833 + j2.075
575	0.919 + j1.088	3.687 + j2.033
600	0.972 + j1.305	3.546 + j1.985
625	1.032 + j1.523	3.411 + j1.931
650	1.101 + j1.741	3.281 + j1.871
675	1.179 + j1.963	3.156 + j1.807
700	1.268 + j2.187	3.036 + j1.738
725	1.371 + j2.416	2.922 + j1.666
750	1.49 + j2.651	2.813 + j1.591
775	1.629 + j2.891	2.708 + j1.512
800	1.792 + j3.138	2.609 + j1.432
825	1.984 + j3.39	2.514 + j1.349
850	2.212 + j3.649	2.423 + j1.264
875	2.484 + j3.91	2.336 + j1.178
900	2.812 + j4.17	2.254 + j1.091
925	3.209 + j4.421	2.175 + j1.003
950	3.689 + j4.648	2.1 + j0.913
975	4.27 + j4.829	2.029 + j0.823
1000	4.967 + j4.927	1.96 + j0.733



### 7.3 Test circuit information

### Table 10. List of components

For test circuit, see Figure 3, Figure 4 and Figure 5.

Component	Description	Value		Remarks
B1, B2	semi rigid coax	25 $Ω$ ; 49.5 mm		UT-090C-25 (EZ 90-25)
C1	multilayer ceramic chip capacitor	12 pF	[1]	
C2, C3, C4, C5, C6	multilayer ceramic chip capacitor	8.2 pF	[1]	
C7	multilayer ceramic chip capacitor	6.8 pF	[2]	
C8	multilayer ceramic chip capacitor	2.7 pF	[2]	
C9	multilayer ceramic chip capacitor	2.2 pF	[2]	
C10, C13, C14	multilayer ceramic chip capacitor	100 pF	[3]	
C11, C12	multilayer ceramic chip capacitor	10 pF	[2]	
C15, C16	multilayer ceramic chip capacitor	4.7 μF, 50 V		Kemet C1210X475K5RAC-TU or capacitor of same quality.
C17, C18, C23, C24	multilayer ceramic chip capacitor	100 pF	[2]	
C19, C20	multilayer ceramic chip capacitor	10 μF, 50 V		TDK C570X7R1H106KT000N or capacitor of same quality.
C21, C22	electrolytic capacitor	470 μF; 63 V		
C30	multilayer ceramic chip capacitor	10 pF	<u>[4]</u>	
C31	multilayer ceramic chip capacitor	9.1 pF	[4]	
C32	multilayer ceramic chip capacitor	3.9 pF	[4]	
C33, C34, C35	multilayer ceramic chip capacitor	100 pF	<u>[4]</u>	
C36, C37	multilayer ceramic chip capacitor	4.7 μF, 50 V		TDK C4532X7R1E475MT020U or capacitor of same quality.
L1	microstrip	-	<u>[5]</u>	$(W \times L)$ 15 mm $\times$ 13 mm
L2	microstrip	-	<u>[5]</u>	$(W \times L)$ 5 mm $\times$ 26 mm
L3, L32	microstrip	-	<u>[5]</u>	(W $\times$ L) 2 mm $\times$ 49.5 mm
L4	microstrip	-	<u>[5]</u>	(W $\times$ L) 1.7 mm $\times$ 3.5 mm
L5	microstrip	-	<u>[5]</u>	(W $\times$ L) 2 mm $\times$ 9.5 mm
L30	microstrip	-	<u>[5]</u>	(W $\times$ L) 5 mm $\times$ 13 mm
L31	microstrip	-	<u>[5]</u>	(W $\times$ L) 2 mm $\times$ 11 mm
L33	microstrip	-	<u>[5]</u>	(W $\times$ L) 2 mm $\times$ 3 mm
R1, R2	wire resistor	10 Ω		

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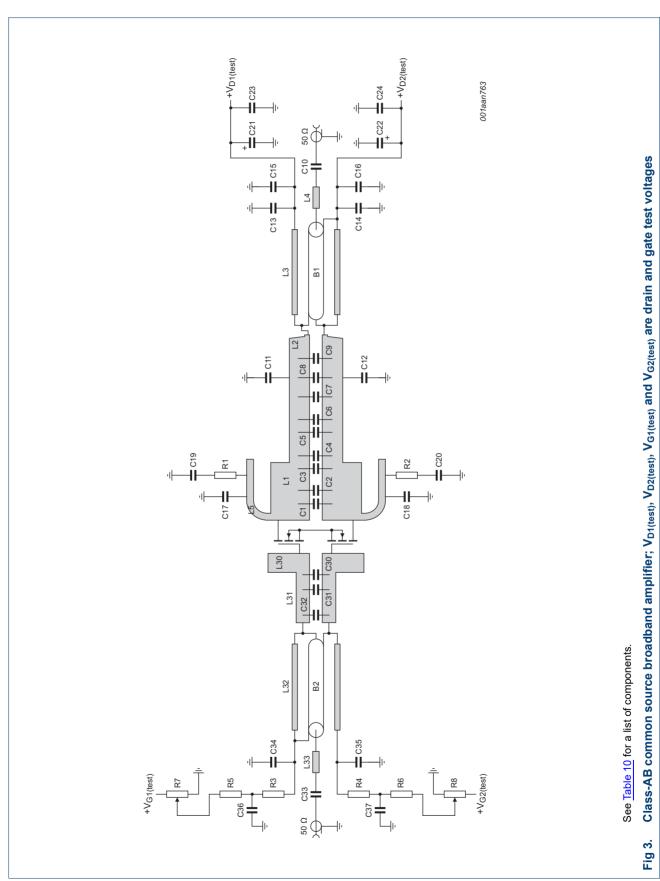
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### Table 10. List of components ... continued

For test circuit, see Figure 3, Figure 4 and Figure 5.

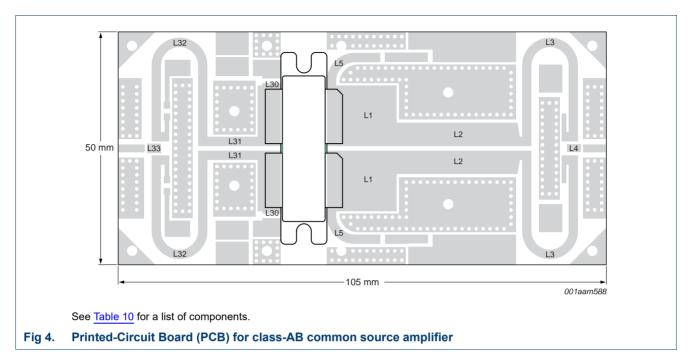
Component	Description	Value	Remarks
R3, R4	SMD resistor	5.6 Ω	0805
R5, R6	wire resistor	100 Ω	
R7, R8	potentiometer	10 kΩ	

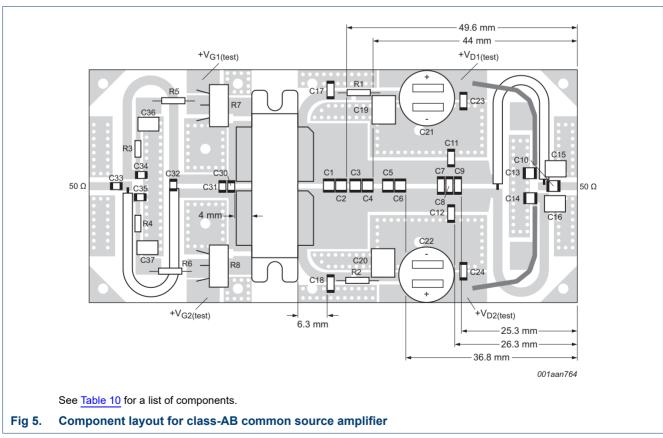
- [1] American technical ceramics type 800R or capacitor of same quality.
- [2] American technical ceramics type 800B or capacitor of same quality.
- [3] American technical ceramics type 180R or capacitor of same quality.
- [4] American technical ceramics type 100A or capacitor of same quality.
- [5] Printed-Circuit Board (PCB): Taconic RF35;  $\epsilon_r$  = 3.5 F/m; height = 0.762 mm; Cu (top/bottom metallization); thickness copper plating = 35  $\mu$ m.



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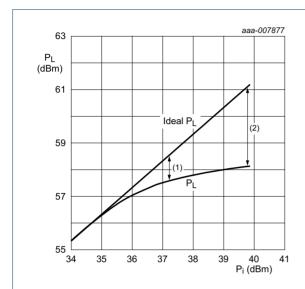
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### 7.4 Graphical data

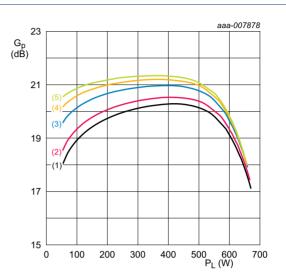
### 7.4.1 Pulsed



 $V_{DS}$  = 50 V;  $I_{Dq}$  = 1300 mA; f = 860 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

- (1)  $P_{L(1dB)} = 57.6 \text{ dBm } (575 \text{ W})$
- (2)  $P_{L(3dB)} = 58.1 \text{ dBm } (649 \text{ W})$

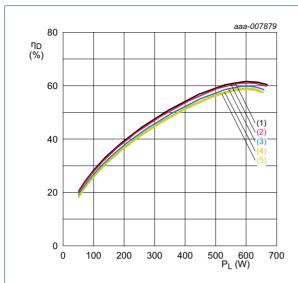
Fig 6. Output power as a function of input power; typical values



 $V_{DS}$  = 50 V; f = 860 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $I_{Dq} = 100 \text{ mA}$
- (2)  $I_{Dq} = 200 \text{ mA}$
- (3)  $I_{Dq} = 600 \text{ mA}$
- (4)  $I_{Dq} = 1000 \text{ mA}$
- (5)  $I_{Dq} = 1300 \text{ mA}$

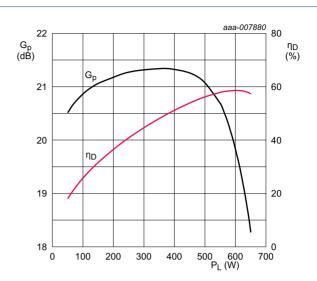
Fig 7. Power gain as a function of output power; typical values



 $V_{DS}$  = 50 V; f = 860 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

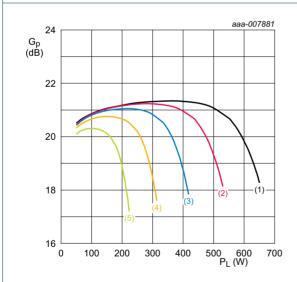
- (1)  $I_{Dq} = 100 \text{ mA}$
- (2)  $I_{Dq} = 200 \text{ mA}$
- (3)  $I_{Dq} = 600 \text{ mA}$
- (4)  $I_{Dq} = 1000 \text{ mA}$
- (5)  $I_{Dq} = 1300 \text{ mA}$





 $V_{DS}$  = 50 V;  $I_{Dq}$  = 1300 mA; f = 860 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

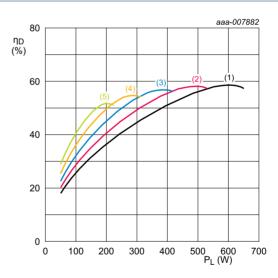
# Fig 9. Power gain and drain efficiency as function of output power; typical values



 $I_{Dq}$  = 1300 mA; f = 860 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $V_{DS} = 50 \text{ V}$
- (2)  $V_{DS} = 45 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 35 \text{ V}$
- (5)  $V_{DS} = 30 \text{ V}$

Fig 10. Power gain as a function of output power; typical values



 $I_{Dq}$  = 1300 mA; f = 860 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

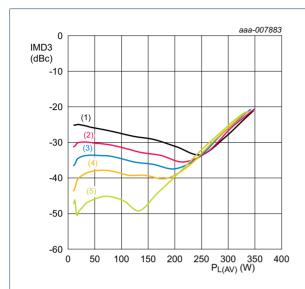
- (1)  $V_{DS} = 50 \text{ V}$
- (2)  $V_{DS} = 45 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 35 V$
- (5)  $V_{DS} = 30 \text{ V}$

Fig 11. Drain efficiency as a function of output power; typical values

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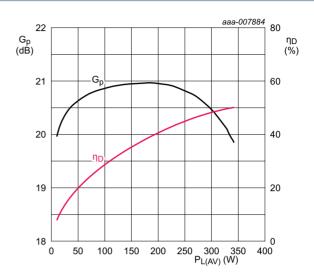
### 7.4.2 2-Tone CW



 $V_{DS}$  = 50 V;  $f_1$  = 860.0 MHz;  $f_2$  = 860.1 MHz.

- (1)  $I_{Dq} = 600 \text{ mA}$
- (2)  $I_{Dq} = 1000 \text{ mA}$
- (3)  $I_{Dq} = 1300 \text{ mA}$
- (4)  $I_{Dq} = 1600 \text{ mA}$
- (5)  $I_{Dq} = 2000 \text{ mA}$

Fig 12. Third-order intermodulation distortion as a function of average output power; typical values



 $V_{DS}$  = 50 V;  $I_{Dq}$  = 1300 mA;  $f_1$  = 860.0 MHz;  $f_2$  = 860.1 MHz.

Fig 13. Power gain and drain efficiency as function of average output power; typical values

**Product data sheet** 

# 8. Package outline

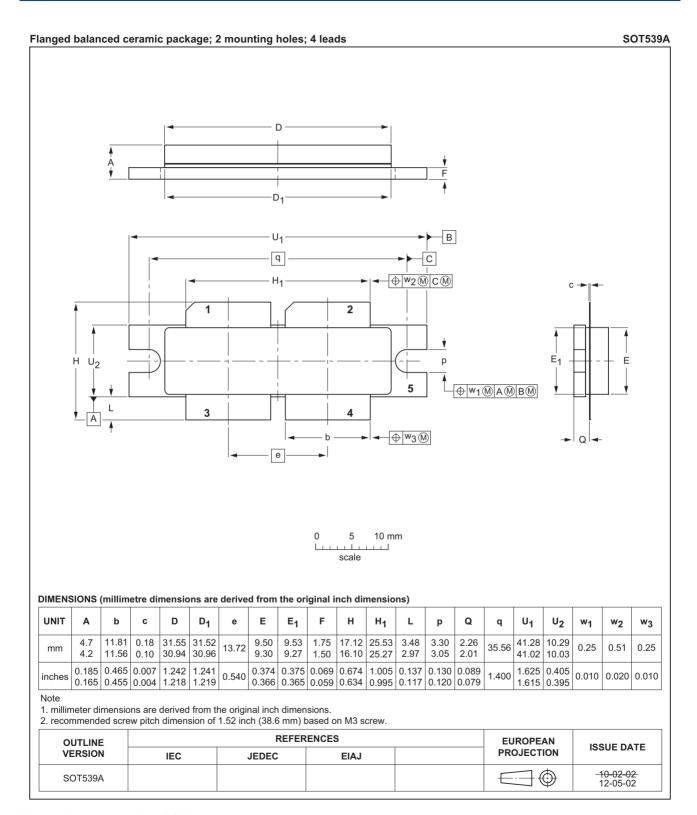


Fig 14. Package outline SOT539A

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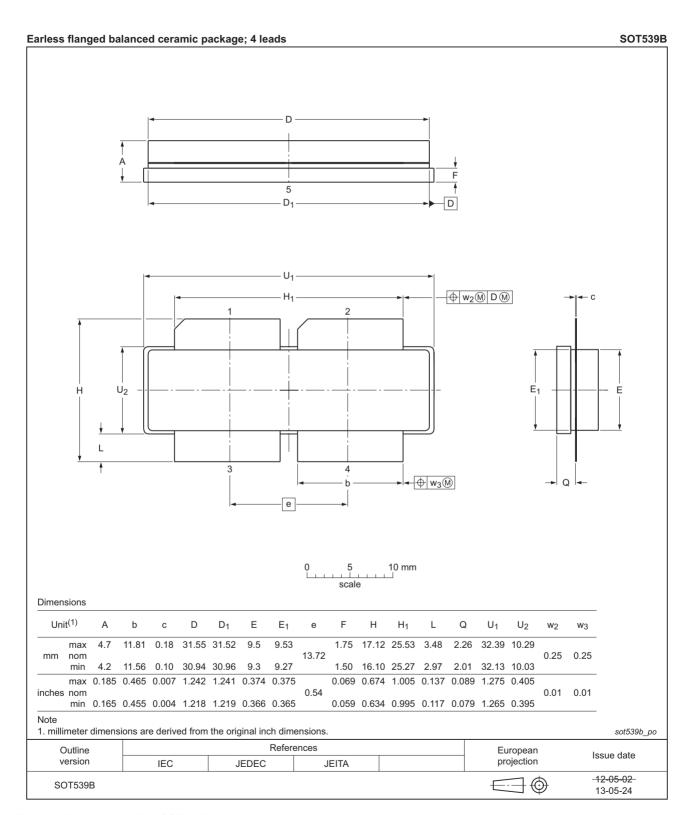


Fig 15. Package outline SOT539B

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# 9. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### 10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

# 11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF988_BLF988S#3	20150901	Product data sheet		BLF988_BLF988S v.2	
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
	• Legal texts n	ave been adapted to the new	company name wne	ere appropriate.	
BLF988_BLF988S v.2	20130801	Product data sheet	-	BLF988_BLF988S v.1	
BLF988_BLF988S v.1	20121009	Objective data sheet	-	-	

# 12. Legal information

### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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